

Title (en)
CR-DOPED SCANDIUM BORATE LASER

Publication
EP 0238904 A3 19890315 (EN)

Application
EP 87103067 A 19870304

Priority
US 84521586 A 19860327

Abstract (en)
[origin: EP0238904A2] A broadly wavelength-tunable laser is provided which comprises as the laser medium a single crystal of $\text{MBO}_3\text{:CR}^{3+}$, where M is selected from the group of Sc, In and Lu. The laser may be operated over a broad temperature range from cryogenic temperatures to elevated temperatures. Emission is in a spectral range from red to infrared, and the laser is useful in the fields of defense, communications, isotope separation, photochemistry, etc.

IPC 1-7
H01S 3/16; H01S 3/091

IPC 8 full level
H01S 3/06 (2006.01); **H01S 3/091** (2006.01); **H01S 3/0915** (2006.01); **H01S 3/094** (2006.01); **H01S 3/106** (2006.01); **H01S 3/16** (2006.01)

CPC (source: EP US)
H01S 3/091 (2013.01 - EP US); **H01S 3/106** (2013.01 - EP US); **H01S 3/16** (2013.01 - EP US); **H01S 3/1623** (2013.01 - EP US)

Citation (search report)
[A] JOURNAL OF CRYSTAL GROWTH, vol. 64, no. 2, November 1983, pages 385-388, North-Holland Publishing Company; K.OKA et al.: "Crystal growth of InBO_3 "

Cited by
CN107573937A

Designated contracting state (EPC)
DE FR GB NL

DOCDB simple family (publication)
EP 0238904 A2 19870930; EP 0238904 A3 19890315; EP 0238904 B1 19920520; AU 583981 B2 19890511; AU 7017887 A 19871001; CA 1280198 C 19910212; DE 3779158 D1 19920625; JP S62232985 A 19871013; US 4841530 A 19890620

DOCDB simple family (application)
EP 87103067 A 19870304; AU 7017887 A 19870319; CA 532711 A 19870323; DE 3779158 T 19870304; JP 7393287 A 19870327; US 84521586 A 19860327